

PUBLICATION NUMBER : 2003068643
PUBLICATION DATE : 07-03-03

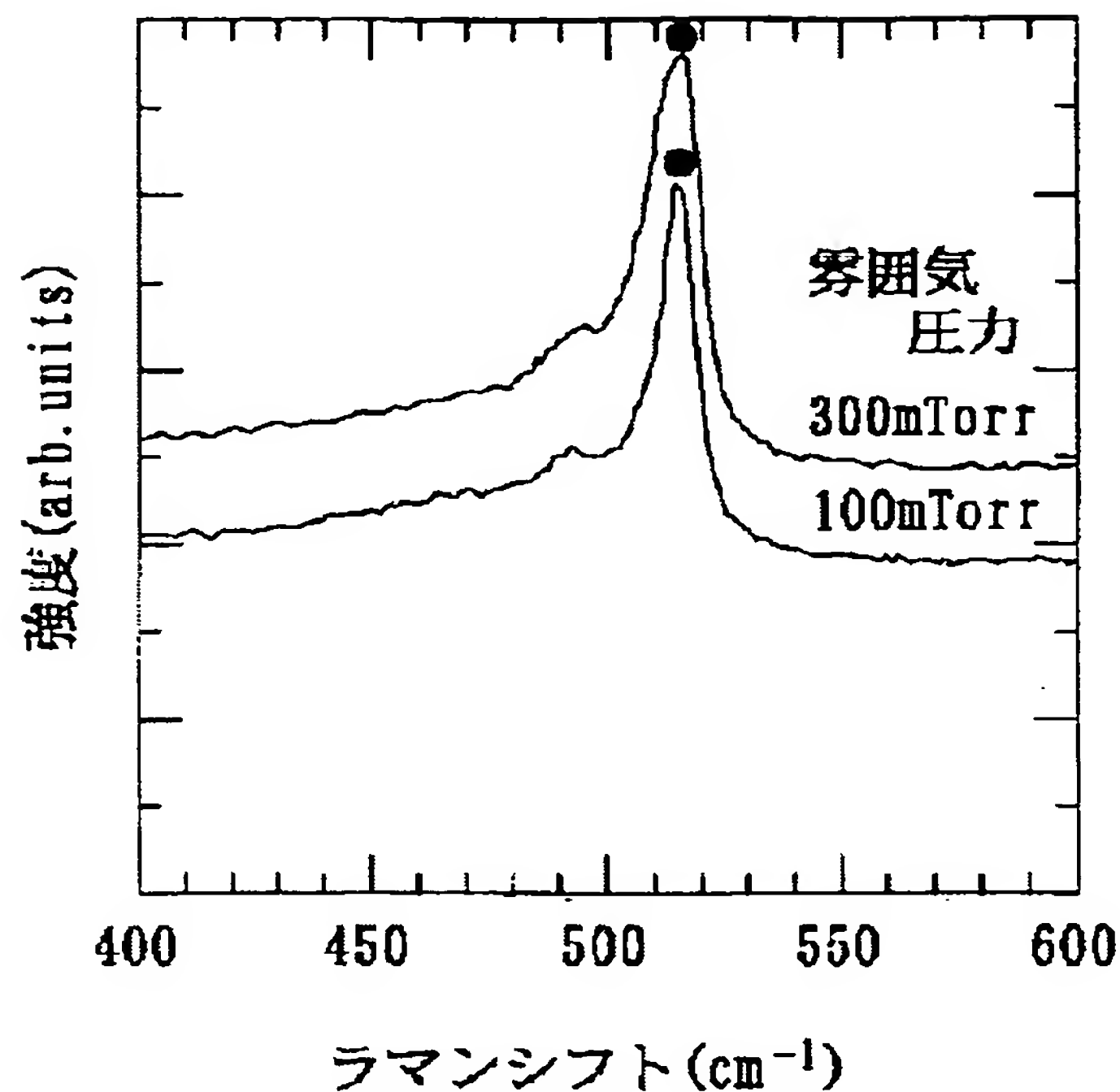
APPLICATION DATE : 23-08-01
APPLICATION NUMBER : 2001252393

APPLICANT : JAPAN ADVANCED INST OF SCIENCE
& TECHNOLOGY HOKURIKU;

INVENTOR : IMAMORI KENSAKU;

INT.CL. : H01L 21/20 H01L 21/205 H01L 31/04 //
C23C 16/24 C23C 16/56

TITLE : METHOD FOR MANUFACTURING
CRYSTALLINE SILICON FILM AND
SOLAR CELL



ABSTRACT : PROBLEM TO BE SOLVED: To provide a novel method for manufacturing a crystalline silicon film on an oxide transparent electrode, without reducing transmittivity.

SOLUTION: An amorphous silicon film is formed on an oxide transparent electrode. Atomic hydrogen is irradiated on the amorphous silicon at an atmospheric pressure of preferably 1 to 1,000 mTorr, so as to crystalline the amorphous silicon film.

COPYRIGHT: (C)2003,JPO